MOSFETs Silicon N-Channel MOS (DTMOS V)

# **TK560P60Y**

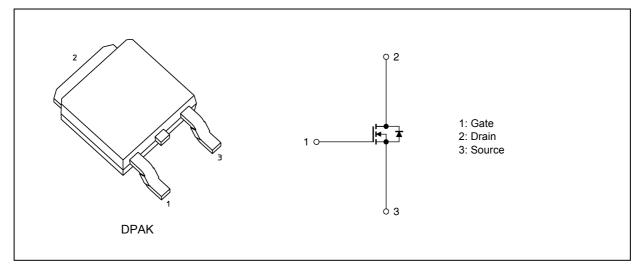
#### 1. Applications

Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.43 \Omega$  (typ.) by using Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
  - (3) Enhancement mode:  $V_{th}$  = 3 to 4 V (V\_{DS} = 10 V,  $I_{D}$  = 0.24 mA)

#### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) ( $T_a = 25 \ ^{\circ}C$ unless otherwise specified)

Characteristics				Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	600	V
Gate-source voltage			V <sub>GSS</sub>	±30	7
Drain current (DC)	(T <sub>c</sub> = 25 °C)	(Note 1)	Ι <sub>D</sub>	7	Α
Drain current (DC)	(T <sub>c</sub> = 100 °C)	(Note 1)	Ι <sub>D</sub>	4.4	Α
Drain current (pulsed)	(T <sub>c</sub> = 25 °C)	(Note 1)	I <sub>DP</sub>	28	Α
Power dissipation	(T <sub>c</sub> = 25 °C)		PD	60	W
Single-pulse avalanche energy		(Note 2)	E <sub>AS</sub>	64	mJ
Single-pulse avalanche current			I <sub>AS</sub>	1.8	Α
Reverse drain current (DC)		(Note 1)	I <sub>DR</sub>	7	1
Reverse drain current (pulsed)		(Note 1)	I <sub>DRP</sub>	28	Α
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

2016-12

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance		2.08	°C/W
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	125	

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V<sub>DD</sub> = 90 V, T<sub>ch</sub> = 25 °C (initial), L = 34.8 mH, R<sub>G</sub> = 25  $\Omega$ , I<sub>AS</sub> = 1.8 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

#### 6. Electrical Characteristics

#### 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±30 V, $V_{DS}$ = 0 V	_	_	±1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	600	_	_	V
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.24 mA	3	_	4	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3.5 A	_	0.43	0.56	Ω

#### 6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 300 V, V <sub>GS</sub> = 0 V, f = 100 kHz		380	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	]		2.5	_	
Output capacitance	C <sub>oss</sub>	]		18	_	
Effective output capacitance	C <sub>o(er)</sub>	$V_{DS}$ = 0 to 400 V, $V_{GS}$ = 0 V	_	30	_	
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN , f = 1 MHz		32	_	Ω
Switching time (rise time)	tr	See Figure 6.2.1	_	20	_	ns
Switching time (turn-on time)	t <sub>on</sub>	]		50	_	
Switching time (fall time)	t <sub>f</sub>	]		8	_	
Switching time (turn-off time)	t <sub>off</sub>	1		105	_	1
MOSFET dv/dt ruggedness	dv/dt	$V_{DS} \leq V_{(BR)DSS}, \ I_D \leq 3.5 \ A$	50	_	_	V/ns

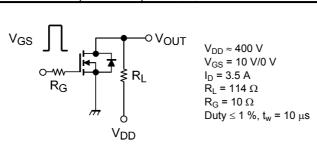


Fig. 6.2.1 Switching Time Test Circuit

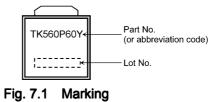
#### 6.3. Gate Charge Characteristics ( $T_a = 25 \,^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 7 \text{ A}$		14.5	—	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	2.3	_	
Gate-drain charge	Q <sub>gd</sub>			7.5	_	

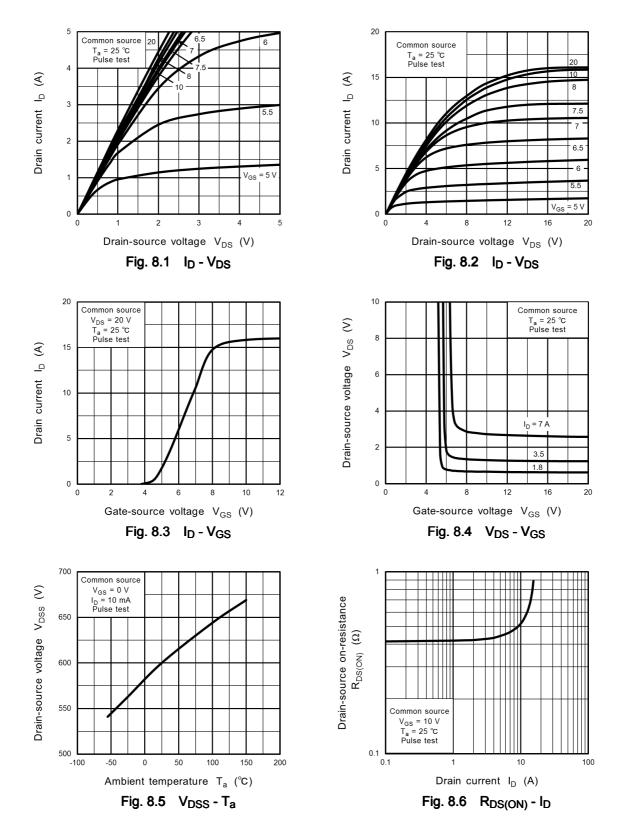
#### 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

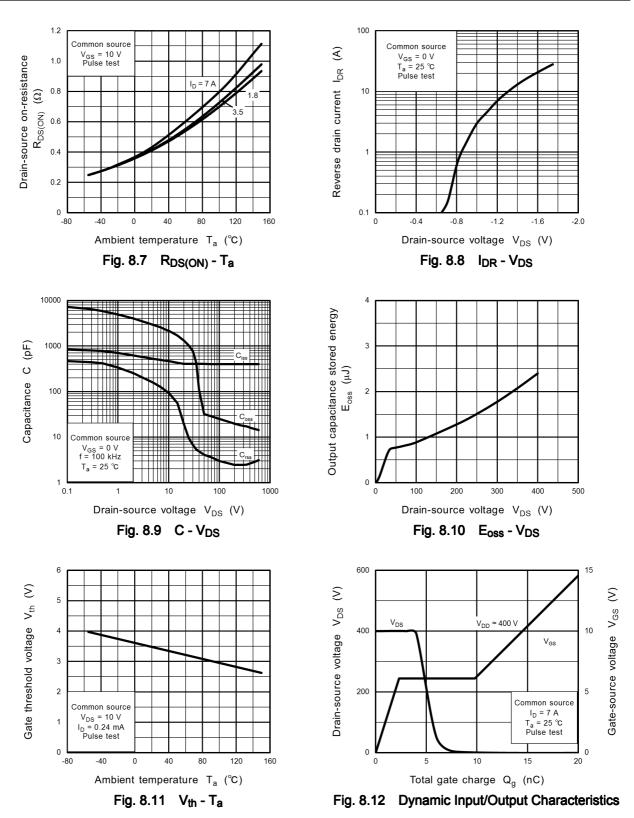
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 7 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	V <sub>DD</sub> ≈ 400 V	_	240	_	ns
Reverse recovery charge	Q <sub>rr</sub>	I <sub>DR</sub> = 3 A, V <sub>GS</sub> = 0 V -dI <sub>DR</sub> /dt = 100 A/μs	_	1.6	_	μC
Peak reverse recovery current	l <sub>rr</sub>		_	14.2	_	А
Diode dv/dt ruggedness	dv/dt	$V_{DS} \leq 400$ V, $I_{DR} \leq 3$ A, $V_{GS}$ = 0 V	15			V/ns

### 7. Marking



#### 8. Characteristics Curves (Note)





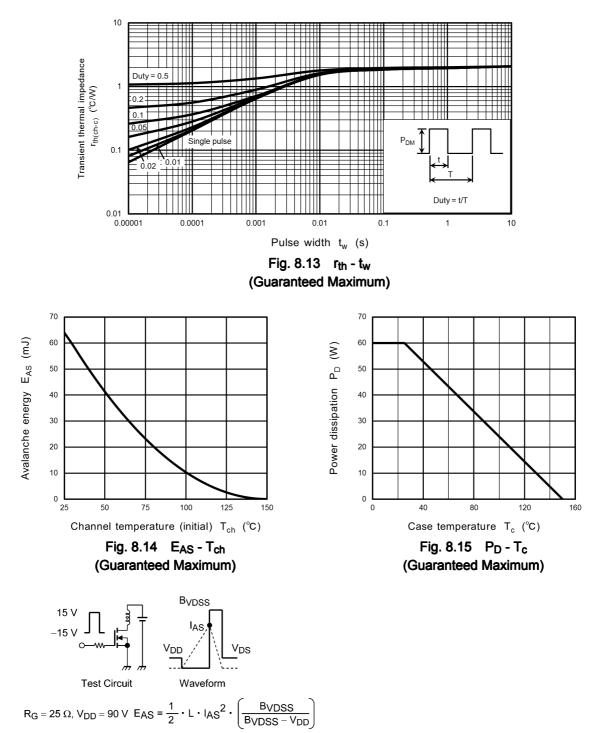
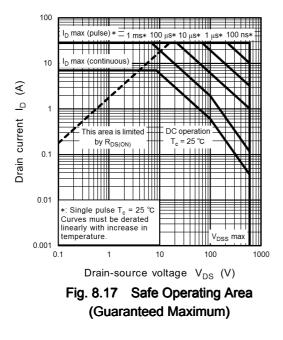


Fig. 8.16 Test Circuit/Waveform



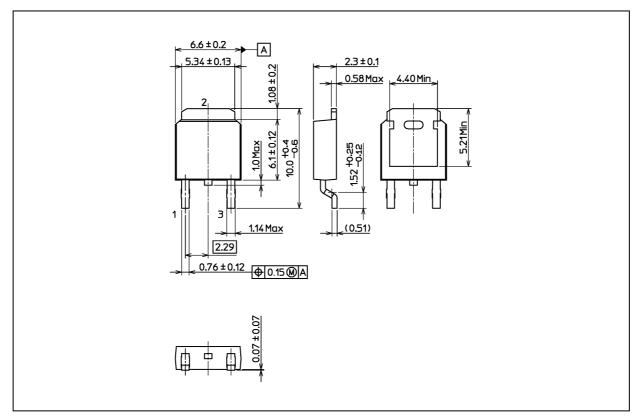
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### TK560P60Y

#### **Package Dimensions**

Unit: mm



Weight: 0.36 g (typ.)

	Package Name(s)	
TOSHIBA: 2-7K1S		
Nickname: DPAK		

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